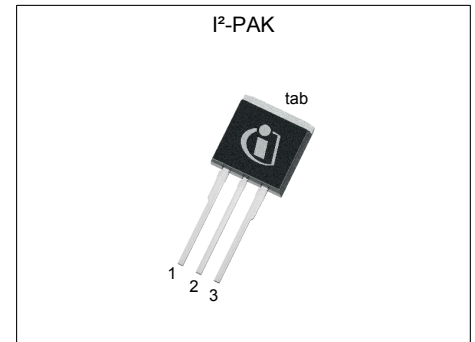


# MOSFET

## OptiMOS™ 3 Power-Transistor, 100 V

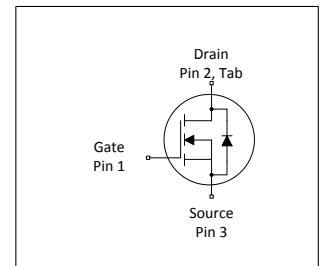
### Features

- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	100	V
$R_{DS(on)}$	8.6	mΩ
$I_D$	82	A



Type / Ordering Code	Package	Marking	Related Links
IPI086N10N3 G	PG-TO 262-3	086N10N	-

<sup>1)</sup> J-STD20 and JESD22

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	82 58	A	$T_C=25\text{ °C}^{1)}$ $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	328	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	110	mJ	$I_D=73\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	125	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j$ , $T_{stg}$	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.2	K/W	-
Thermal resistance, junction - ambient, minimal footprint	$R_{thJA}$	-	-	62	K/W	-
Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	50	K/W	-

## 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	2.7	3.5	V	$V_{DS}=V_{GS}$ , $I_D=75\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	7.4 9.3	8.6 15.4	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=73\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=36\text{ A}$ , TO 262
Gate resistance	$R_G$	-	1	-	$\Omega$	-
Transconductance	$g_{fs}$	45	89	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=80\text{ A}$

<sup>1)</sup> See Diagram 3

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	2990	3980	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	523	696	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	-	21	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	18	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=73\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Rise time	$t_r$	-	42	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=73\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	31	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=73\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Fall time	$t_f$	-	8	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=73\text{ A}$ , $R_{G,ext}=1.6\ \Omega$

**Table 6 Gate charge characteristics<sup>1)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	15	-	nC	$V_{DD}=50\text{ V}$ , $I_D=73\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	8	-	nC	$V_{DD}=50\text{ V}$ , $I_D=73\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	14	-	nC	$V_{DD}=50\text{ V}$ , $I_D=73\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	42	55	nC	$V_{DD}=50\text{ V}$ , $I_D=73\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=50\text{ V}$ , $I_D=73\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	55	73	nC	$V_{DD}=50\text{ V}$ , $V_{GS}=0\text{ V}$

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	82	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	328	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	1.0	1.2	V	$V_{GS}=0\text{ V}$ , $I_F=80\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	71	-	ns	$V_R=50\text{ V}$ , $I_F=73\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	-	123	-	nC	$V_R=50\text{ V}$ , $I_F=73\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> See "Gate charge waveforms" for parameter definition

## 4 Electrical characteristics diagrams

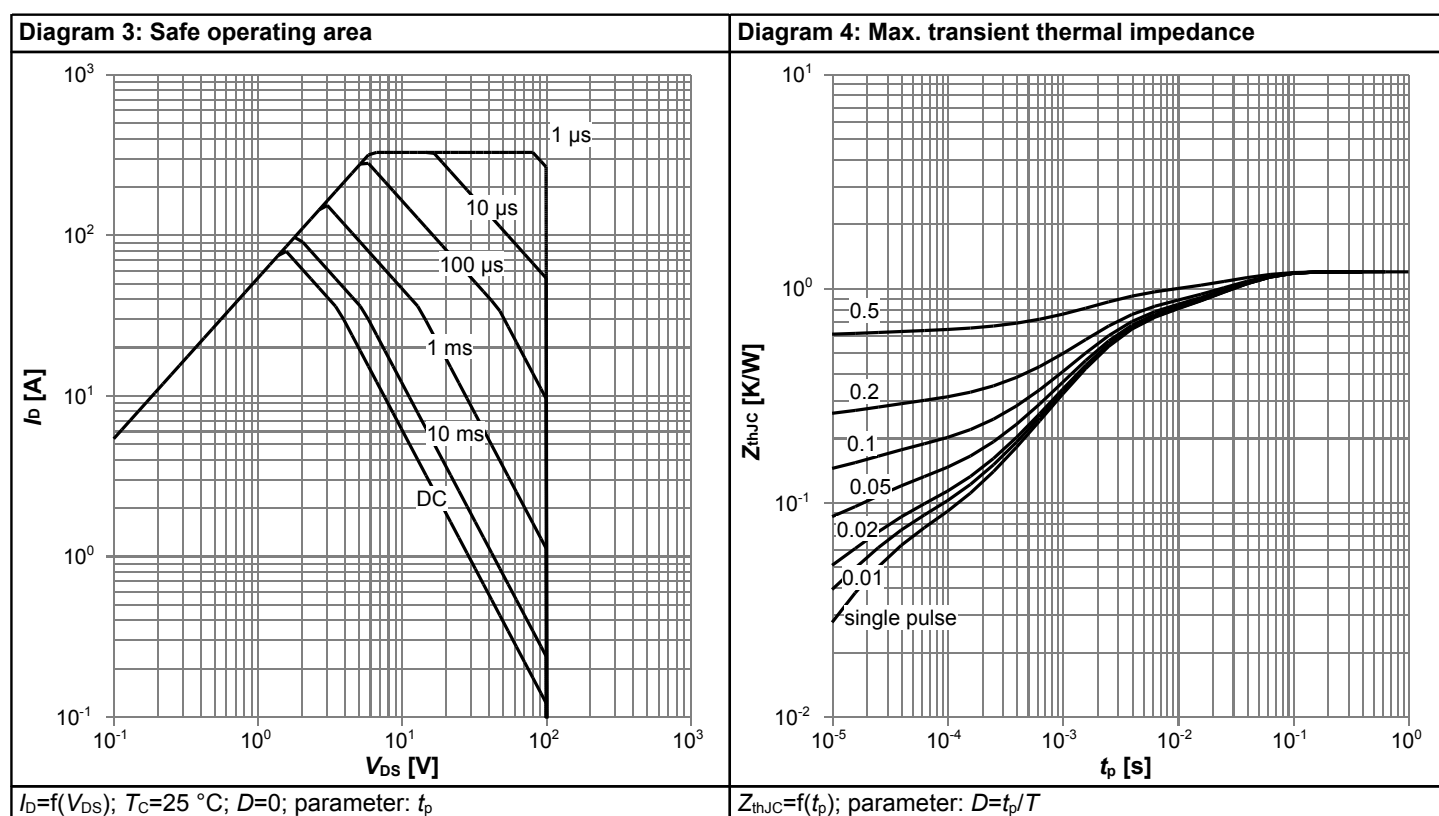
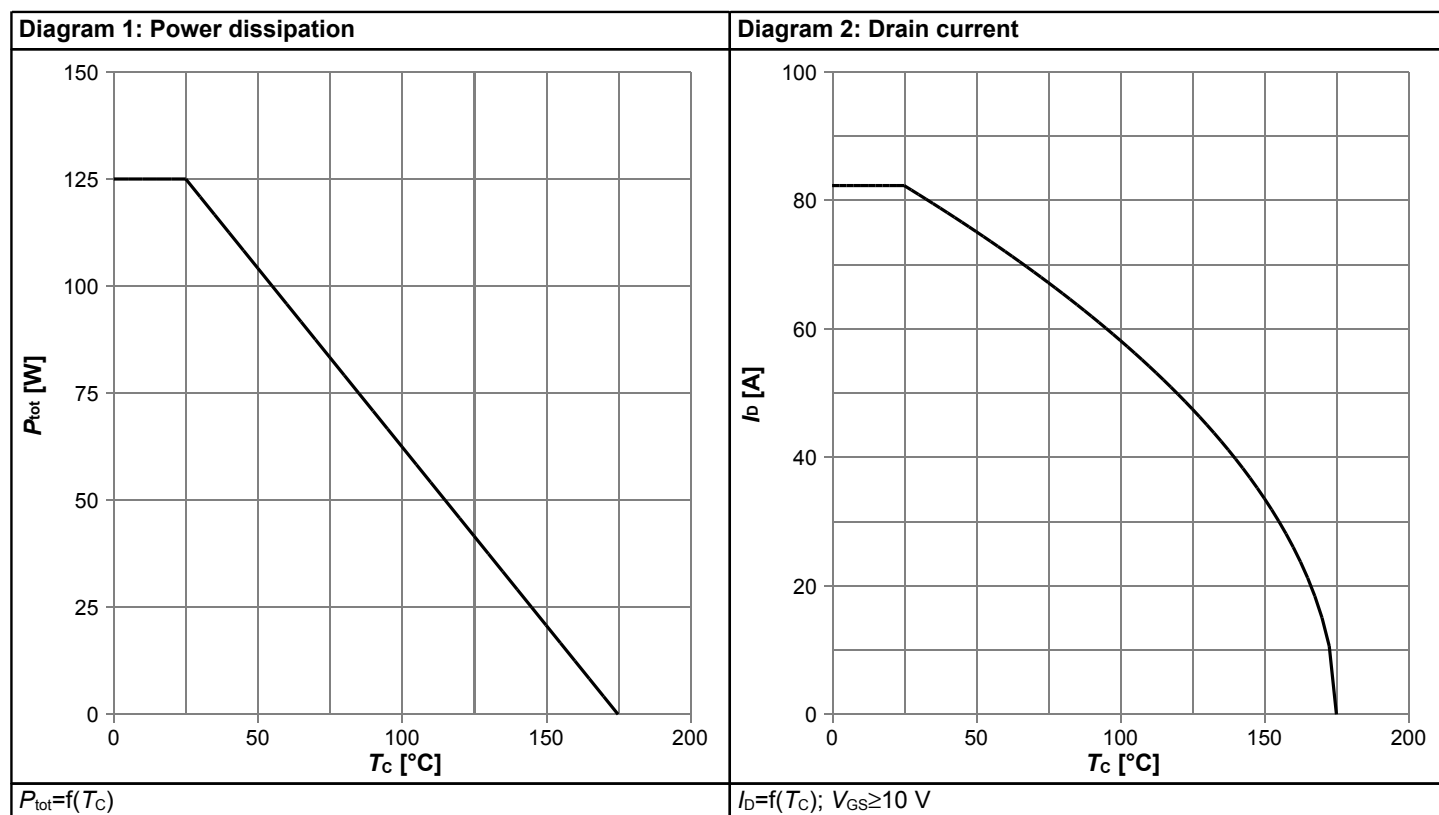
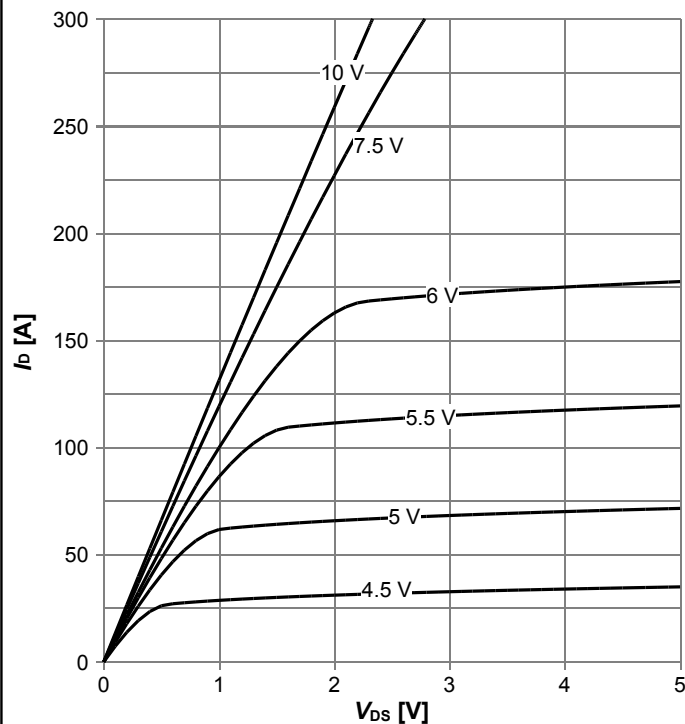
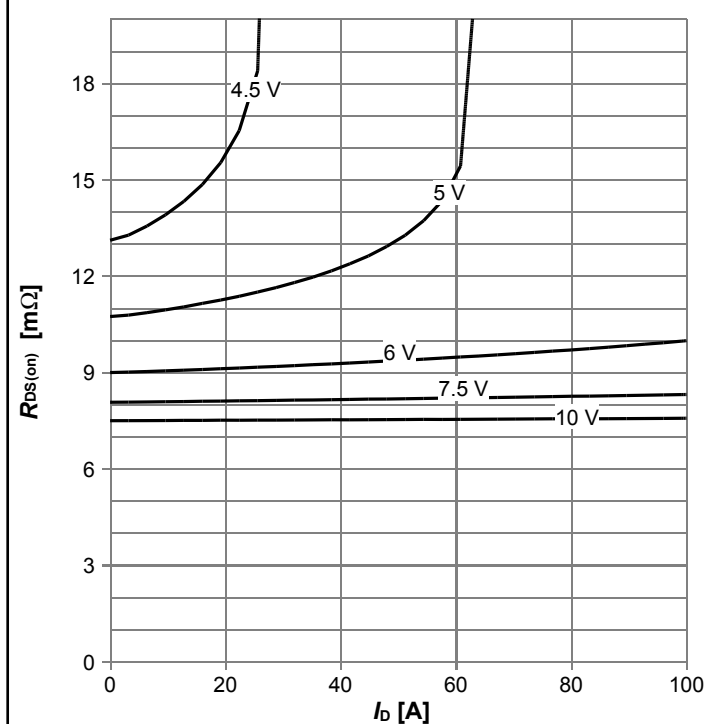


Diagram 5: Typ. output characteristics



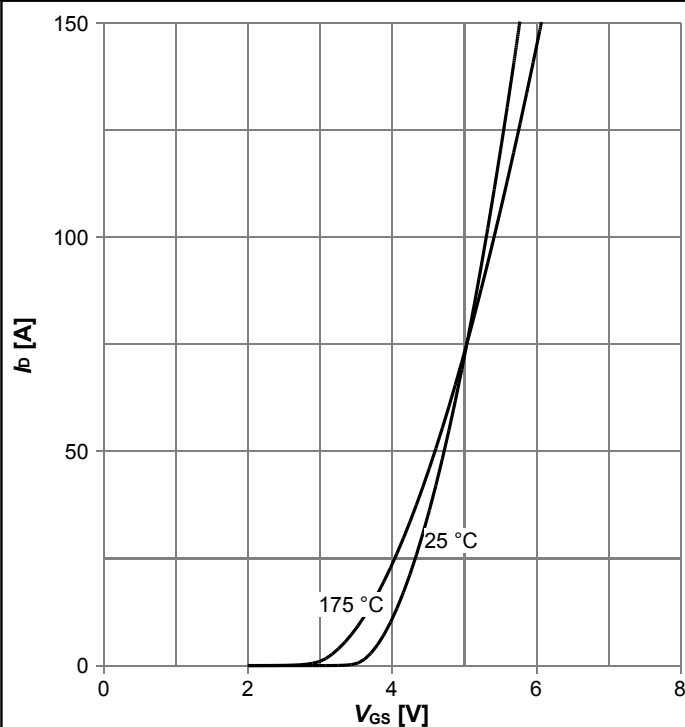
$I_D = f(V_{DS})$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



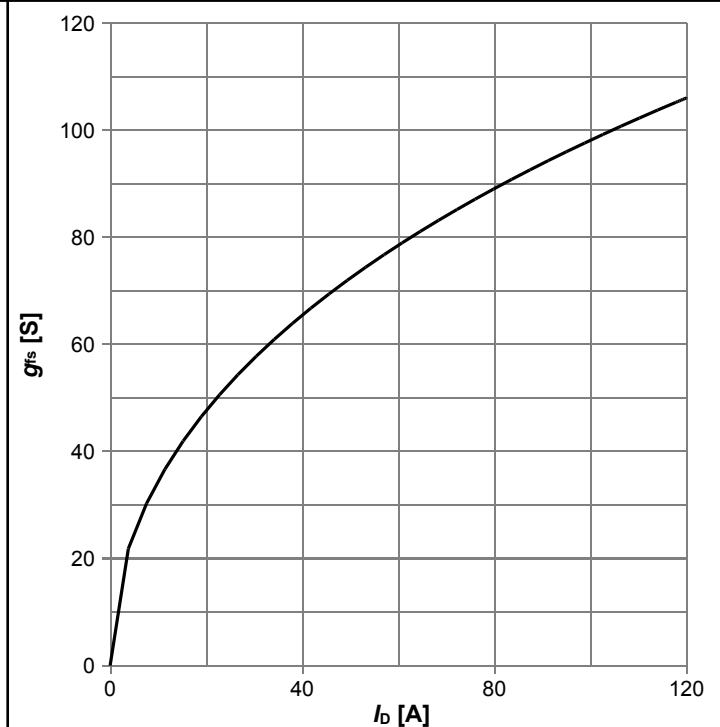
$R_{DS(on)} = f(I_D)$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



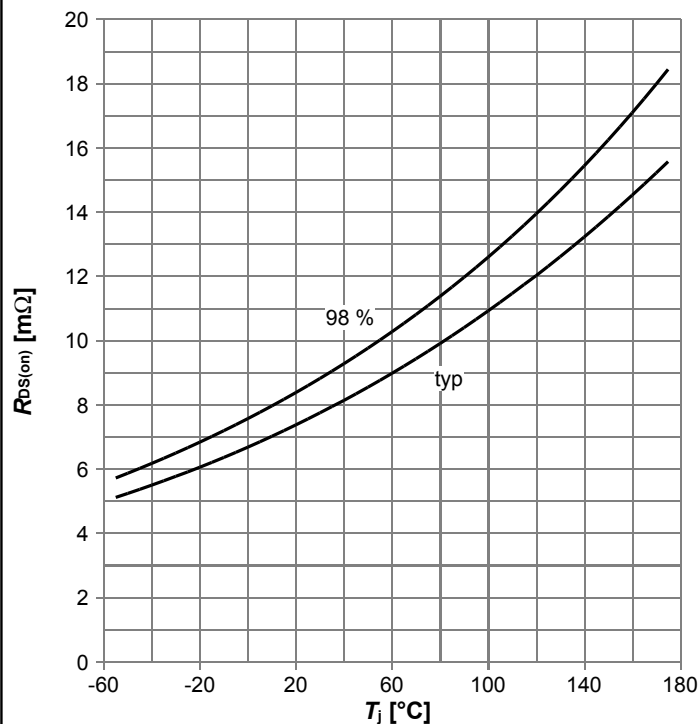
$I_D = f(V_{GS})$ ;  $|V_{DS}| > 2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. forward transconductance



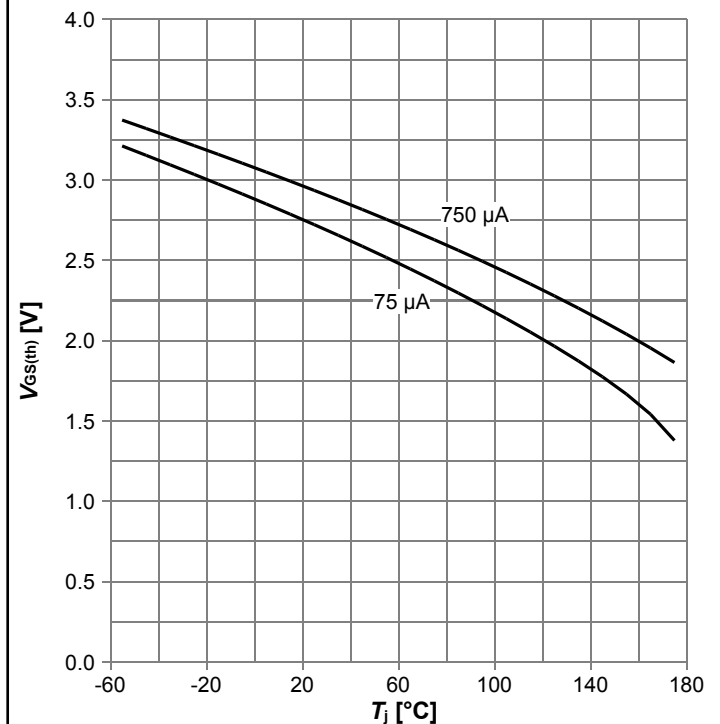
$g_{fs} = f(I_D)$ ;  $T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



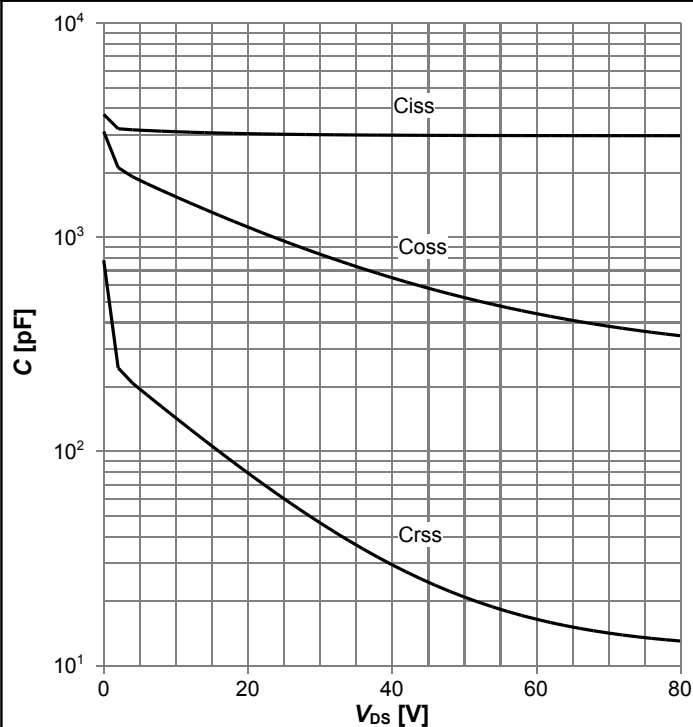
$R_{DS(on)} = f(T_j)$ ;  $I_D = 73$  A;  $V_{GS} = 10$  V

Diagram 10: Typ. gate threshold voltage



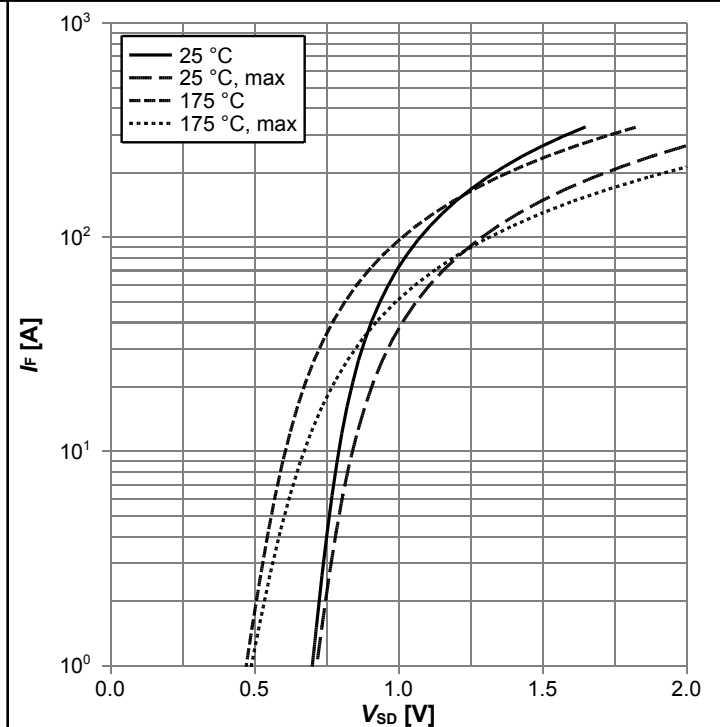
$V_{GS(th)} = f(T_j)$ ;  $V_{GS} = V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



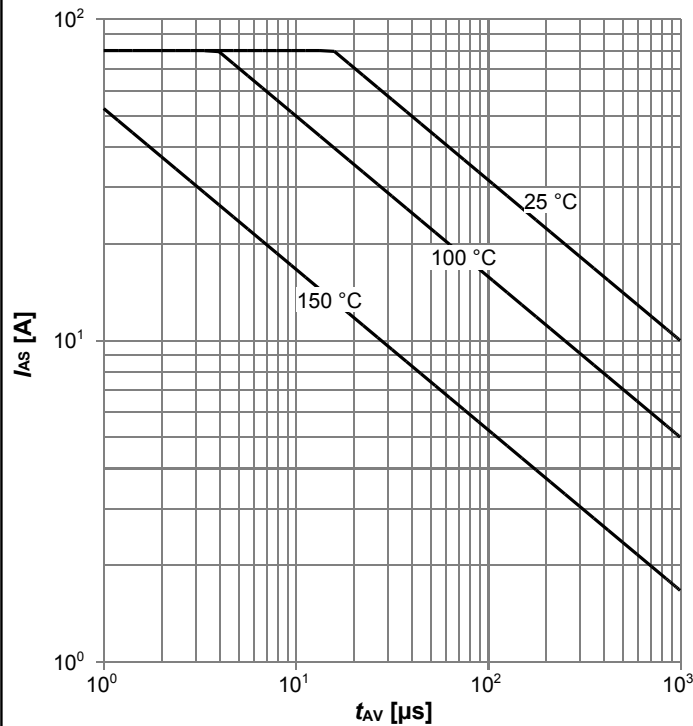
$C = f(V_{DS})$ ;  $V_{GS} = 0$  V;  $f = 1$  MHz

Diagram 12: Forward characteristics of reverse diode



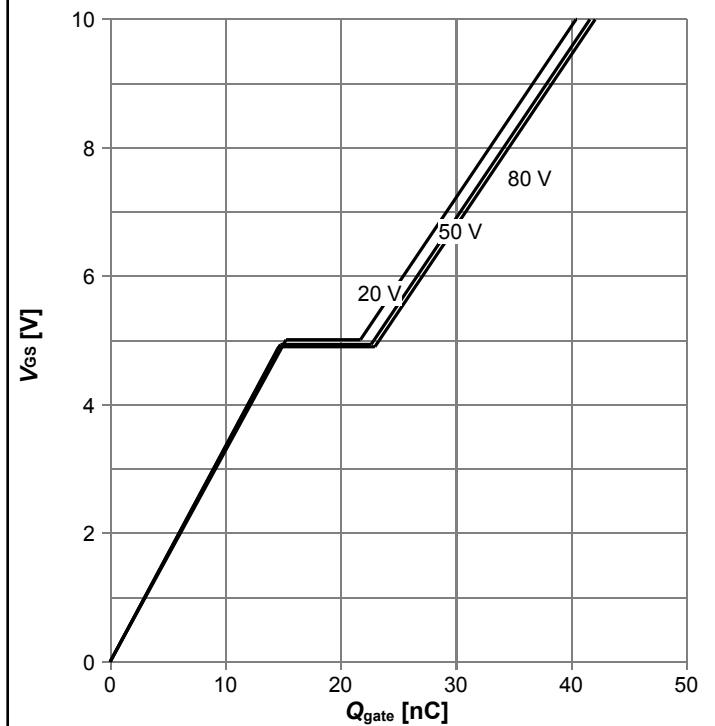
$I_F = f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics



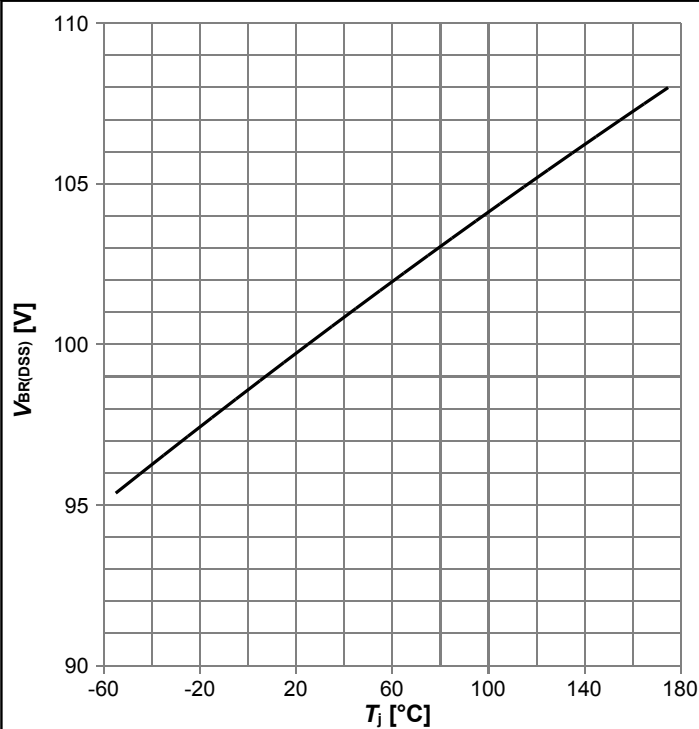
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25\ \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



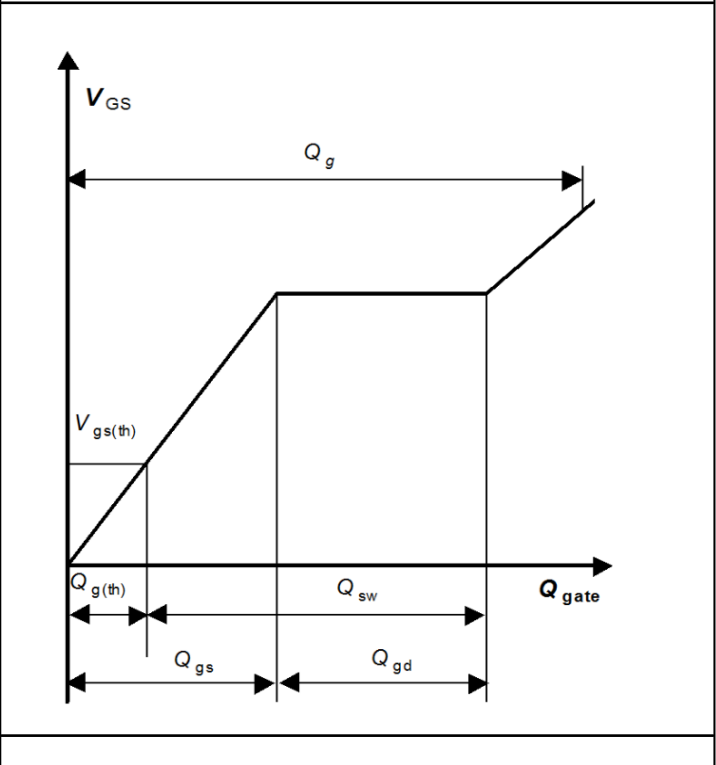
$V_{GS}=f(Q_{gate})$ ;  $I_D=73\text{ A}$  pulsed; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



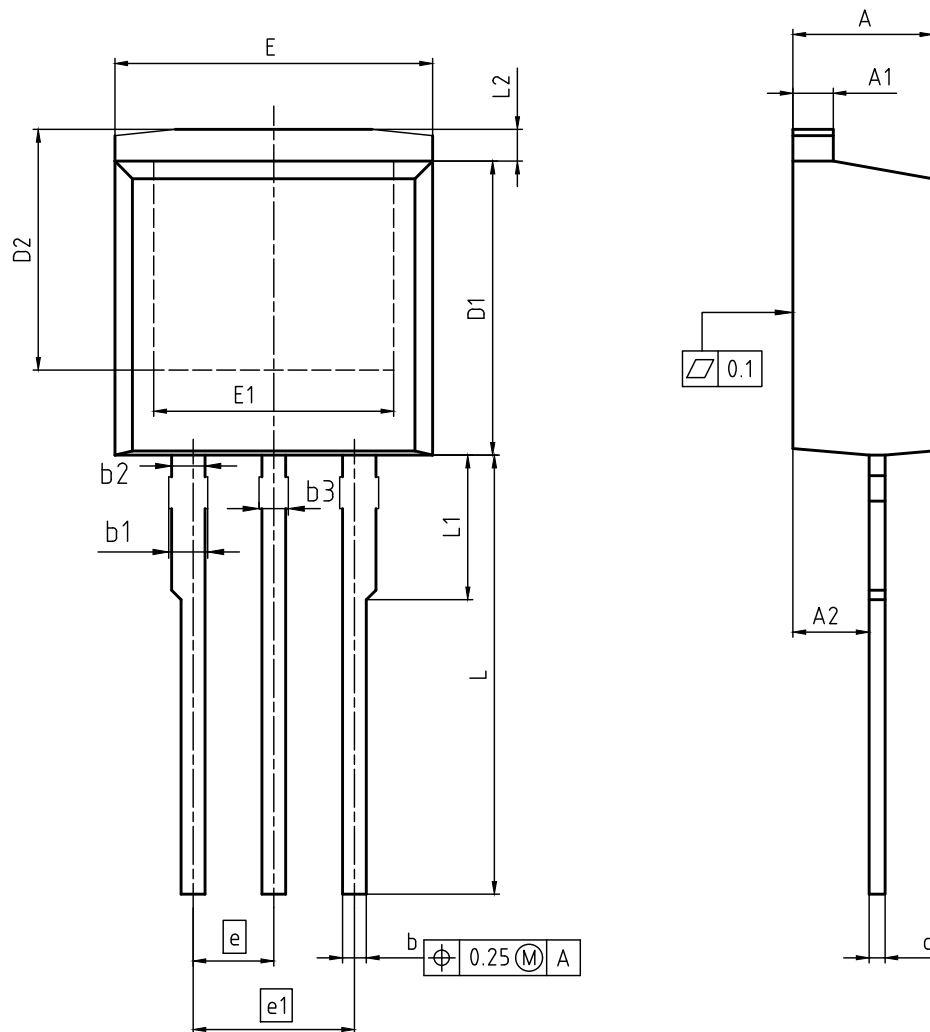
$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1\text{ mA}$

Diagram Gate charge waveforms





## 5 Package Outlines



DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.30	4.57
A1	1.17	1.40
A2	2.15	2.72
b	0.65	0.86
b1	0.95	1.40
b2	0.95	1.15
b3	0.65	1.15
c	0.33	0.60
D1	8.51	9.45
D2	6.90	-
E	9.70	10.36
E1	6.50	8.60
e	2.54	
e1	5.08	
N	3	
L	13.00	14.00
L1	-	4.80
L2	-	1.73

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Figure 1 Outline PG-TO 262-3, dimensions in mm

## Revision History

IPI086N10N3 G

**Revision: 2019-02-08, Rev. 2.7**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.7	2019-02-08	Update product current and package outline

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